

SIDC38D60C6

Fast switching diode chip in EMCON 3 -Technology

FEATURES:

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- 600V EMCON 3 technology 70 µm chip
- soft, fast switching • low reverse recovery charge

small temperature coefficient

- This chip is used for:
- power module •



Applications:

• drives

Chip Type	V _R	I _F	Die Size	Package
SIDC38D60C6	600V	150A	7.8 x 4.9 mm ²	sawn on foil

MECHANICAL PARAMETER:

Raster size	7.8 x 4.9				
Area total / active	38.22 / 33.38	mm ²			
Anode pad size	7.1 x 4.2				
Thickness	70	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	353 pcs				
Passivation frontside	Photoimide				
Anode metallization	3200 nm AlSiCu				
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤500µm				
Reject ink dot size	Ø 0.65mm; max 1.2mm				
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V _{RRM}		600	V
Continuous forward current limited by	1_		1)	
T _{jmax}	/ _F			А
Maximum repetitive forward current	1		300	
limited by T _{jmax}	IFRM		300	
Operating junction and storage temperature	T_{j} , T_{stg}		-40+175	°C

¹⁾ depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), T_j =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
Falameter	Symbol	Cond	luons	min.	Тур.	max. 27	
Reverse leakage current	I _R	V _R =600V	<i>T_j</i> =25 ° <i>C</i>			27	μA
Cathode-Anode breakdown Voltage	V _{Br}	I _R =0.25mA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V _F	I _F =150A	<i>T_j</i> =25 ° <i>C</i>	1.2	1.6	1.9	V

Dynamic Electrical Characteristics (verified by design/characterization), inductive load

Parameter	Symbol	Condi	Value ²⁾			Unit	
Falailletei	Symbol	Conai	min.	Тур.	max.		
Peak reverse recovery current	I _{RM}	$I_F = 150A$ di/dt = 5400A/ms $V_R = 300V$ $V_{GE} = -15V$	$T_j = 25 \ ^\circ C$ $T_j = 125 \ ^\circ C$ $T_j = 150 \ ^\circ C$		150 180 185		A
Recovered charge	Q _r	$I_F = 150A$ di/dt = 5400A/ms $V_R = 300V$ $V_{GE} = -15V$	$T_j = 25 \ ^\circ C$ $T_j = 125 \ ^\circ C$ $T_j = 150 \ ^\circ C$		7.00 13.0 15.0		μC
Reverse recovery energy	E _{rec}	$I_F = 150A$ di/dt = 5400A/ms $V_R = 300V$ $V_{GE} = -15V$	$T_j = 25 \ ^\circ C$ $T_j = 125 \ ^\circ C$ $T_j = 150 \ ^\circ C$		1.95 3.50 3.95		mJ

²⁾ values also influenced by parasitic L- and C- in measurement and package.



CHIP DRAWING:





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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet

FS150R06KE3

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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